

Silicon NPN Power Transistors

2SD898

DESCRIPTION

- With TO-3 package
- Built-in damper diode
- High voltage ,high power dissipation
- Wide area of safe operation

APPLICATIONS

- For TV horizontal deflection output applications

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

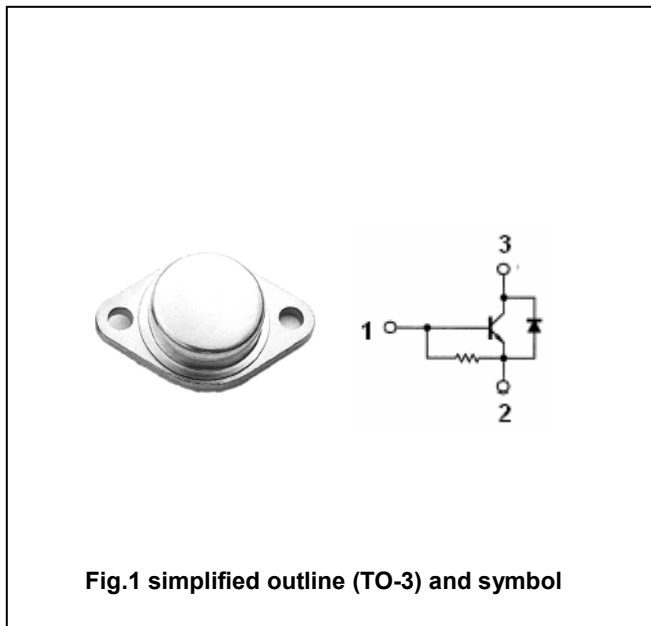


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	1500	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		3	A
I _{CM}	Collector current-peak		3.5	A
P _T	Total power dissipation	T _C =25□	50	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =200mA; I _C =0;	6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =2.5A; I _B =0.8 A			5.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =2.5A; I _B =0.8 A			1.5	V
I _{CES}	Collector cut-off current	V _{CE} =1500V; R _{BE} =0			0.5	mA
I _{EBO}	Emitter cut-off current	V _{EB} =6V; I _C =0	50		200	mA
h _{FE}	DC current gain	I _C =0.5A ; V _{CE} =5V	10		40	
V _F	Diode forward voltage	I _F =3A			2.2	V

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PACKAGE OUTLINE

